

III B. Tech I Semester Supplementary Examinations, July -2023**BASIC ELECTRONICS**

(Common to EEE,ME,CSE,IT,CS,CSE(AI),CSE(AI&ML),CSE(DS),CSE(IOT))

Time: 3 hours

Max. Marks: 70

Answer any **FIVE** Questions **ONE** Question from **Each unit**

All Questions Carry Equal Marks

UNIT-I

1. a) Distinguish between conductors, semiconductors, insulators using energy band diagram. [7M]

b) Explain the filtering action of a capacitor input filter. [7M]

(OR)

2. a) Describe the behaviour of pn junction under Forward bias and reverse bias. [7M]

b) Derive the expression for ripple factor and efficiency of a full wave rectifier. [7M]

UNIT-II

3. a) Explain the working principle of tunnel diode. [7M]

b) State and explain the applications of optical diodes. [7M]

(OR)

4. a) Explain the applications of zener diode. [7M]

b) Explain the structure, characteristics tunnel diode. [7M]

UNIT-III

5. a) Draw and explain the input and output characteristics of a transistor in CE configuration. [7M]

b) Describe how amplification achieved by a BJT [7M]

(OR)

6. a) Explain the working of PNP transistor. [7M]

b) Distinguish between the different types of transistor configurations with necessary circuit diagrams [7M]

UNIT-IV

7. a) Describe the construction and explain the operation of depletion mode MOSFET. Also draw the static characteristics [9M]

b) Compare P-channel JFET with N-channel JFET. [5M]

(OR)

8. a) Explain the working of a P channel JFET and draw the V-I characteristics of it. [9M]

b) Compare P-channel JFET with BJT. [5M]

UNIT-V

9. a) Explain the two-transistor analogy of SCR. [7M]

b) Write about photo transistor. [7M]

(OR)

10. a) Draw the switching characteristics of SCR and explain. [7M]

b) With neat circuit diagram explain the principle operation of UJT. [7M]

